
2SK3069

Silicon N Channel MOS FET
High Speed Power Switching

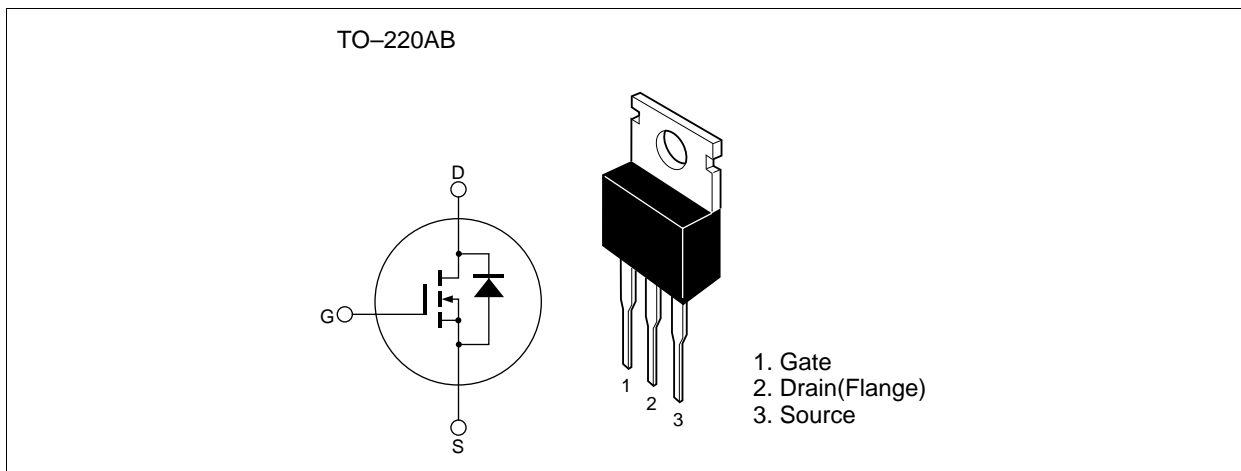
HITACHI

ADE-208-694G (Z)
8th. Edition
Nov. 1998

Features

- Low on-resistance
 $R_{DS(on)} = 6m\Omega$ typ.
- Low drive current
- 4V gate drive device can be driven from 5V source

Outline



2SK3069

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	60	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	75	A
Drain peak current	I _{D(pulse)} ^{Note 1}	300	A
Body-drain diode reverse drain current	I _{DR}	75	A
Avalanche current	I _{AP} ^{Note 3}	50	A
Avalanche energy	E _{AR} ^{Note 3}	214	mJ
Channel dissipation	P _{ch} ^{Note 2}	100	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

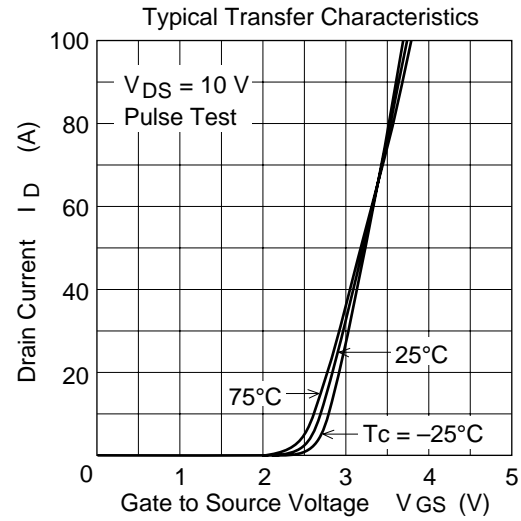
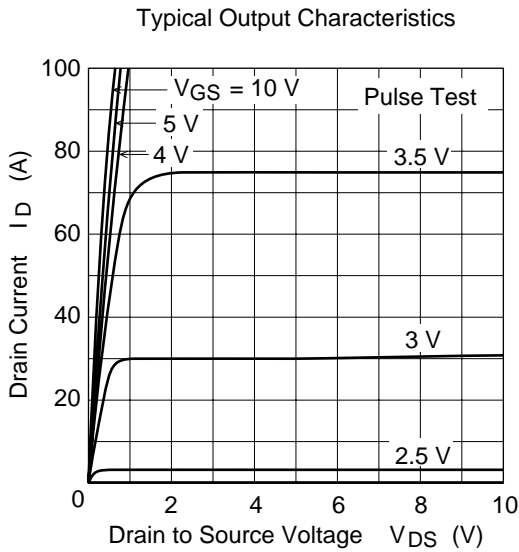
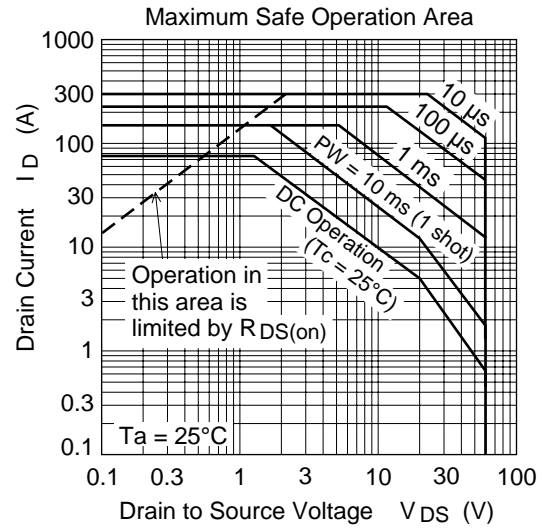
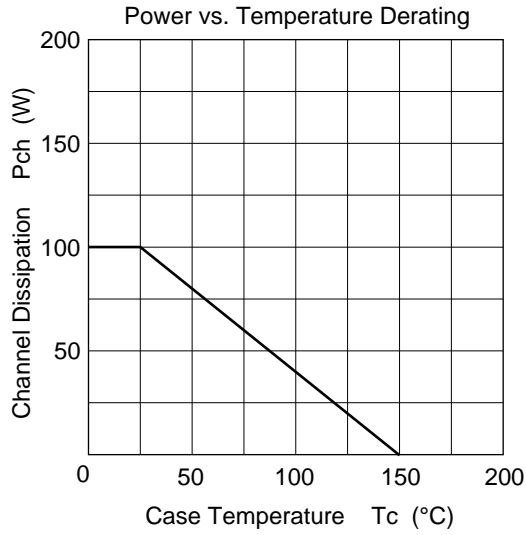
Note: 1. PW ≤ 10μs, duty cycle ≤ 1 %
2. Value at Tc = 25°C
3. Value at Tch = 25°C, Rg ≥ 50Ω

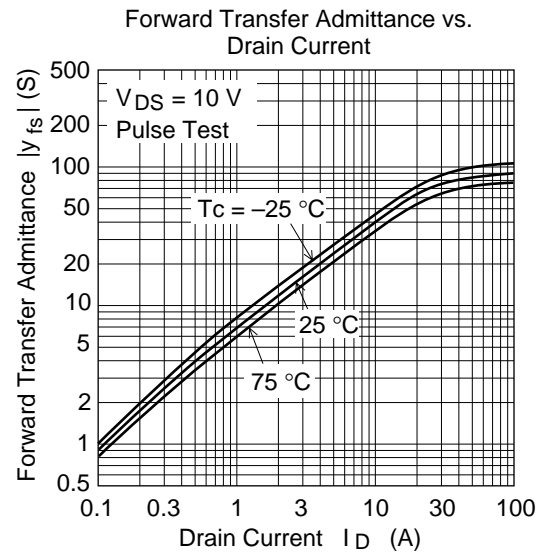
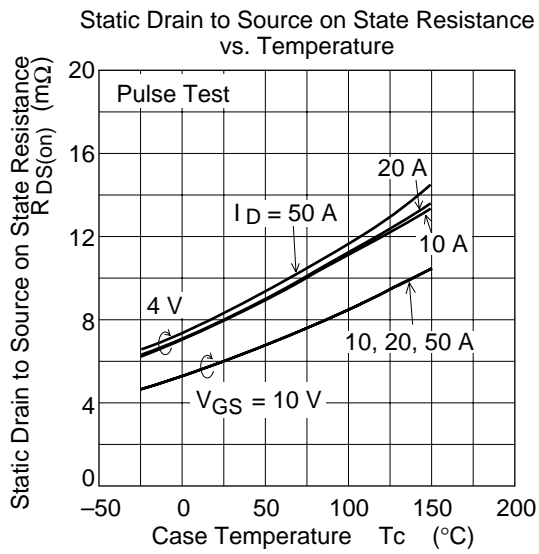
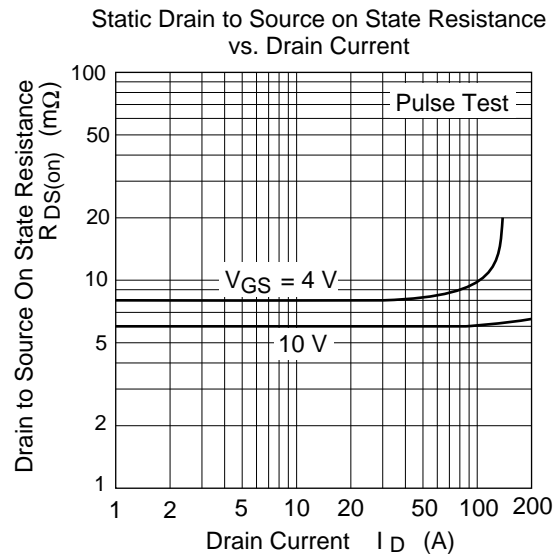
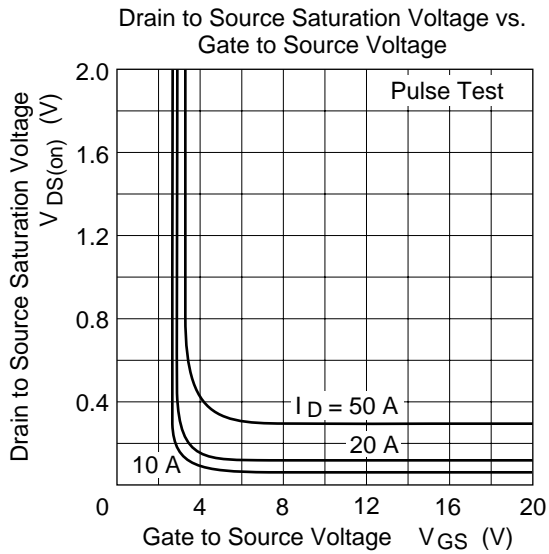
Electrical Characteristics (Ta = 25°C)

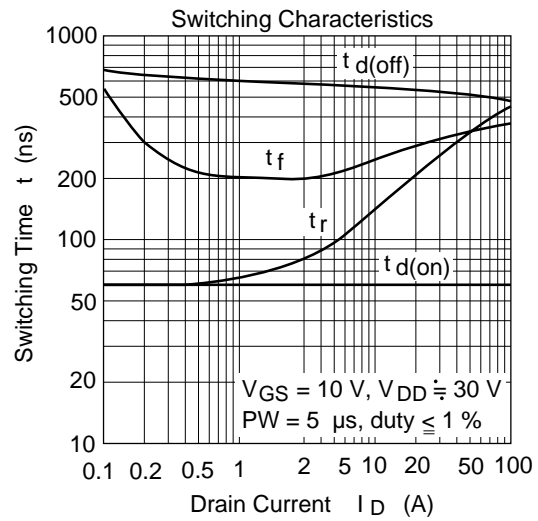
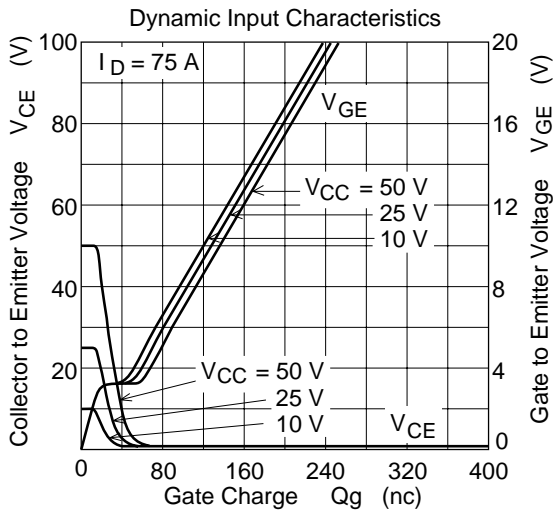
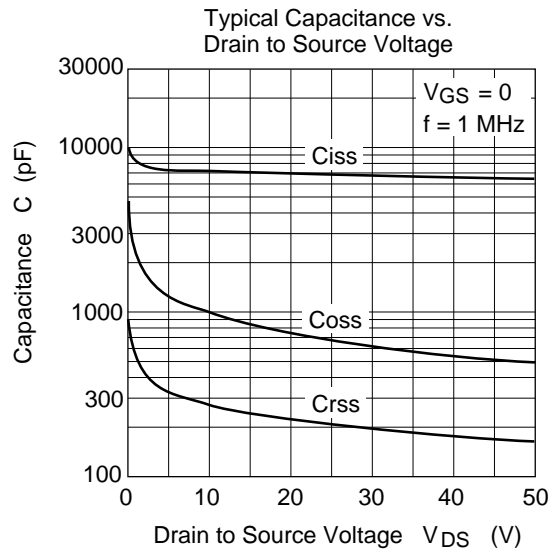
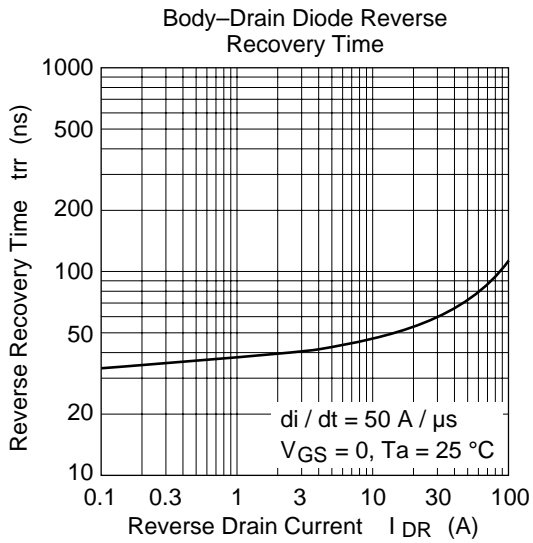
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 10\text{mA}, V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 60\text{V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.5	V	$I_D = 1\text{mA}, V_{DS} = 10\text{V}$ ^{Note 1}
Static drain to source on state resistance	$R_{DS(on)}$	—	6.0	7.5	$\text{m}\Omega$	$I_D = 40\text{A}, V_{GS} = 10\text{V}$ ^{Note 1}
		—	8.0	12	$\text{m}\Omega$	$I_D = 40\text{A}, V_{GS} = 4\text{V}$ ^{Note 1}
Forward transfer admittance	$ y_{fs} $	50	80	—	S	$I_D = 40\text{A}, V_{DS} = 10\text{V}$ ^{Note 1}
Input capacitance	C_{iss}	—	7100	—	pF	$V_{DS} = 10\text{V}$
Output capacitance	C_{oss}	—	1000	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	280	—	pF	$f = 1\text{MHz}$
Total gate charge	Q_g	—	125	—	nc	$V_{DD} = 25\text{V}$
Gate to source charge	Q_{gs}	—	25	—	nc	$V_{GS} = 10\text{V}$
Gate to drain charge	Q_{gd}	—	25	—	nc	$I_D = 75\text{A}$
Turn-on delay time	$t_{d(on)}$	—	60	—	ns	$V_{GS} = 10\text{V}, I_D = 40\text{A}$
Rise time	t_r	—	300	—	ns	$R_L = 0.75\Omega$
Turn-off delay time	$t_{d(off)}$	—	520	—	ns	
Fall time	t_f	—	330	—	ns	
Body-drain diode forward voltage	V_{DF}	—	1.05	—	V	$I_F = 75\text{A}, V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	90	—	ns	$I_F = 75\text{A}, V_{GS} = 0$ $diF/dt = 50\text{A}/\mu\text{s}$

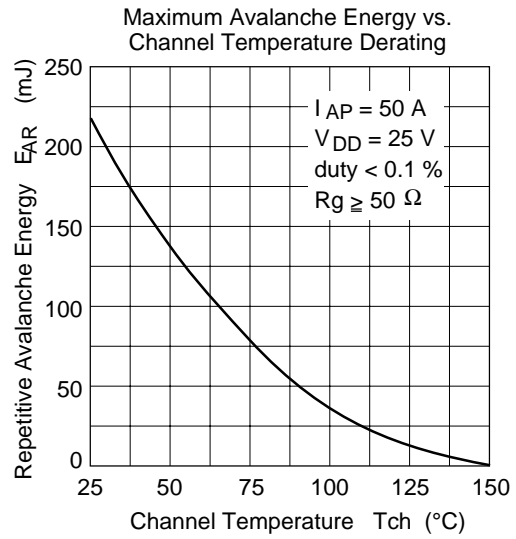
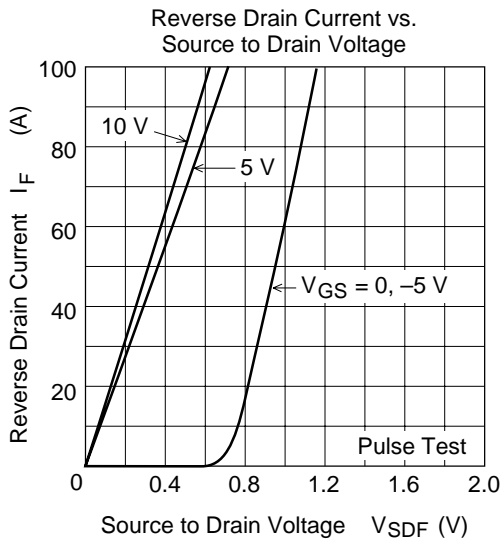
Note: 1. Pulse test

Main Characteristics

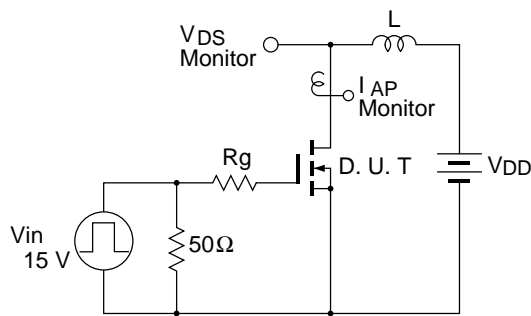






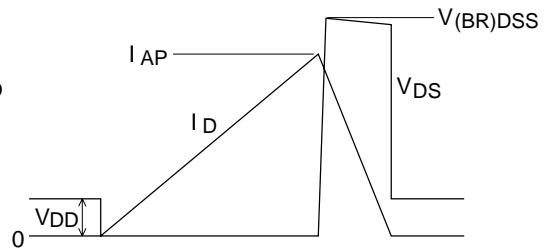


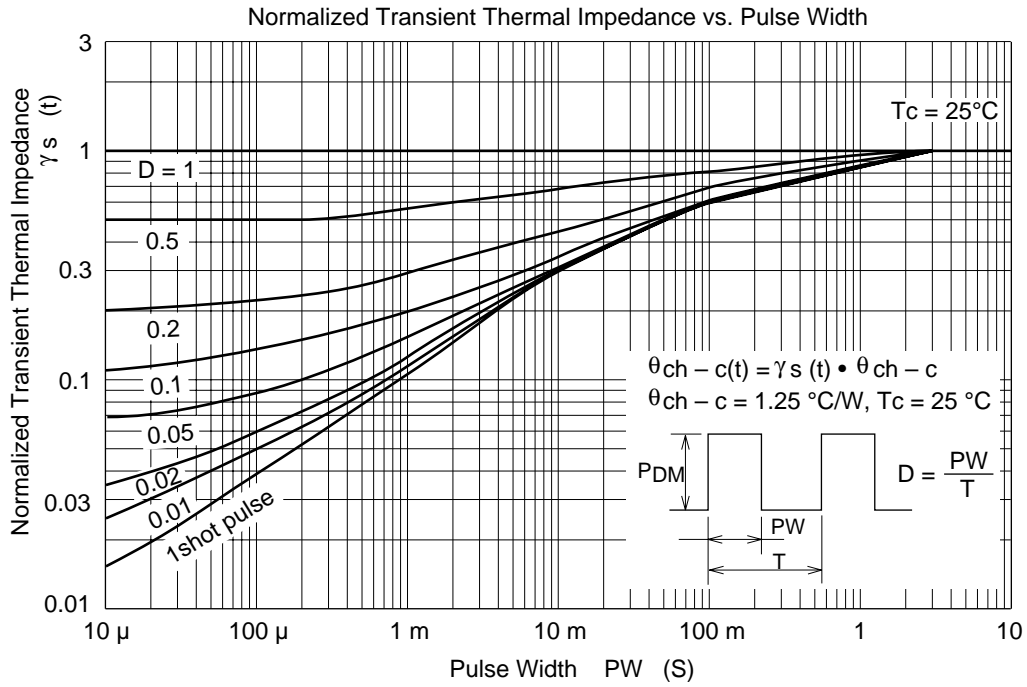
Avalanche Test Circuit



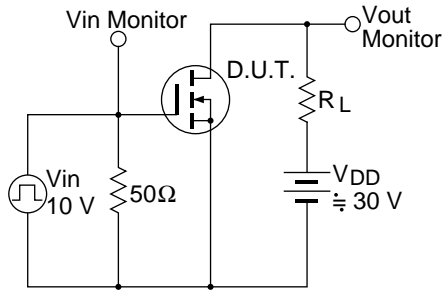
Avalanche Waveform

$$E_{AR} = \frac{1}{2} \cdot L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$

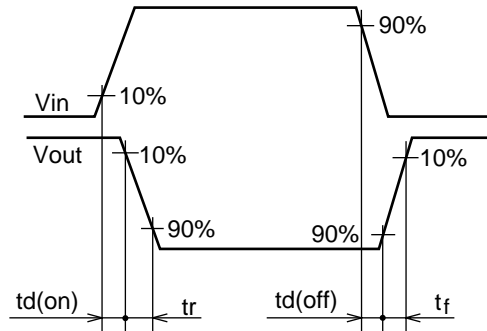




Switching Time Test Circuit

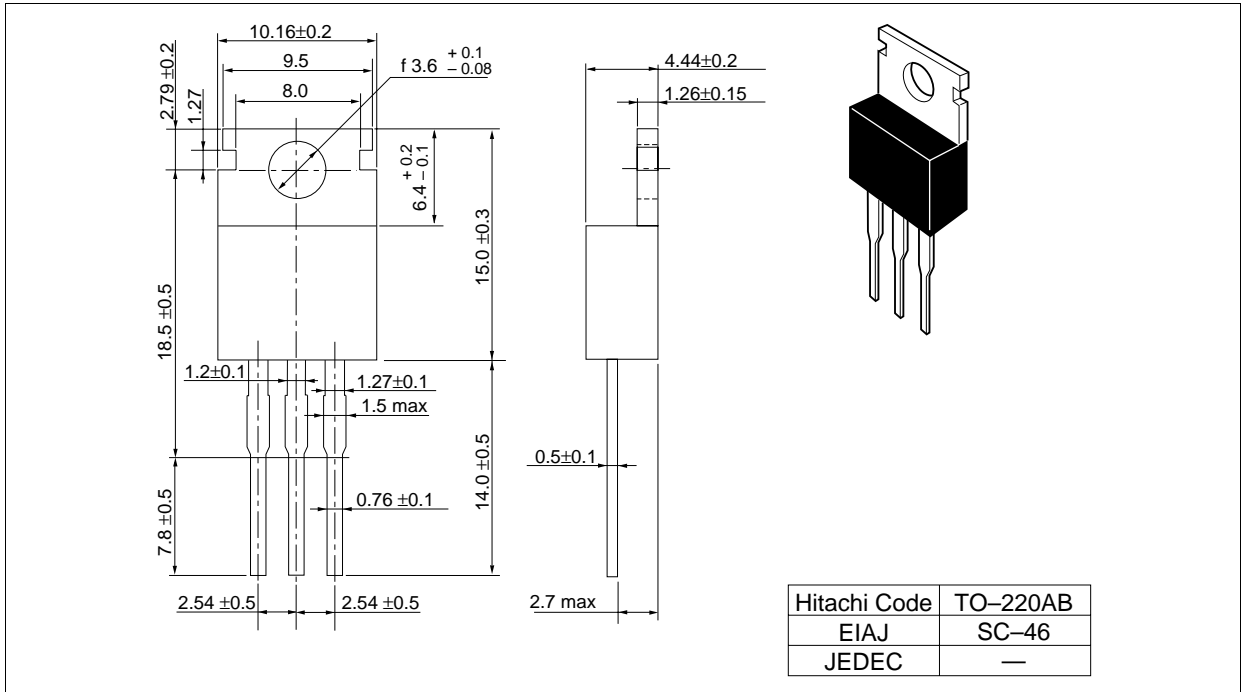


Waveform



Package Dimensions

Unit: mm



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